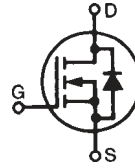


# Polar™ HiperFET™ Power MOSFET

## IXFR16N120P

$V_{DSS} = 1200V$   
 $I_{D25} = 9A$   
 $R_{DS(on)} \leq 1.04\Omega$   
 $t_{rr} \leq 300ns$

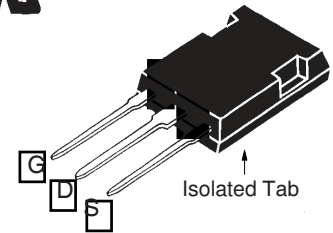
(Electrically Isolated Tab)



N-Channel Enhancement Mode  
Fast Intrinsic Rectifier

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	1200	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	1200	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	9	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	35	A
$I_A$	$T_C = 25^\circ C$	8	A
$E_{AS}$	$T_C = 25^\circ C$	800	mJ
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	15	V/ns
$P_D$	$T_C = 25^\circ C$	230	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$V_{ISOL}$	50/60 Hz, 1 Minute	2500	V~
$F_C$	Mounting Force	20..120/4.5..27	N/lb.
<b>Weight</b>		5	g

ISOPLUS247  
E153432



G = Gate    D = Drain  
S = Source

### Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- Low Intrinsic Gate Resistance
- 2500V~ Electrical Isolation
- International Standard Packages
- Fast Recovery Diode
- Avalanche Rated
- Low Package Inductance

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- High Voltage Switch-mode and Resonant-Mode Power Supplies
- High Voltage Pulse Power Applications
- High Voltage Discharge Circuits in Lasers Pulsers, Spark Igniters, RF Generators
- High Voltage DC-DC converters
- High Voltage DC-AC inverters

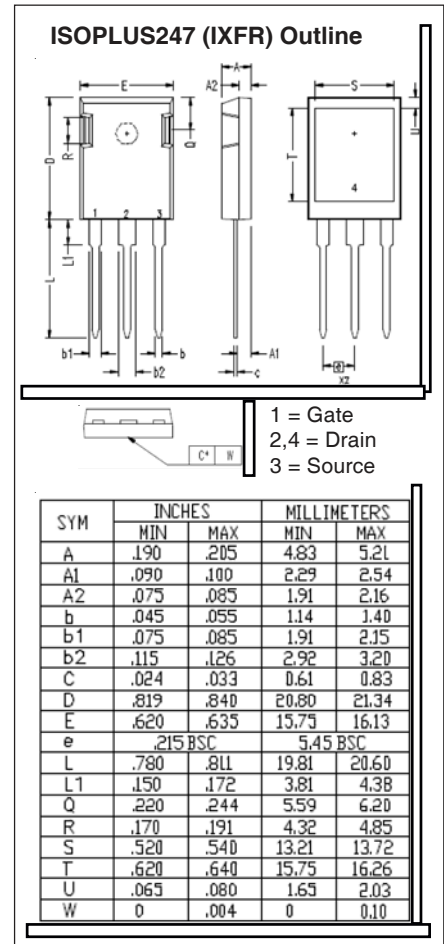
Symbol	Test Conditions ( $T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	1200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 1mA$	3.5		6.5 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			25 $\mu A$ 2.5 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 8A$ , Note 1			1.04 $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{V}, I_D = 8\text{A}$ , Note 1	11	17	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		6900	pF
$C_{oss}$			390	pF
$C_{rss}$			48	pF
$R_{Gi}$	Gate Input Resistance		1.4	$\Omega$
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 8\text{A}$ $R_G = 2\Omega$ (External)		35	ns
$t_r$			28	ns
$t_{d(off)}$			66	ns
$t_f$			35	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 8\text{A}$		120	nC
$Q_{gs}$			37	nC
$Q_{gd}$			47	nC
$R_{thJC}$				0.54 $^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			16 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			64 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 8\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			300 ns
$I_{RM}$			7.5	A
$Q_{RM}$			0.75	$\mu\text{C}$

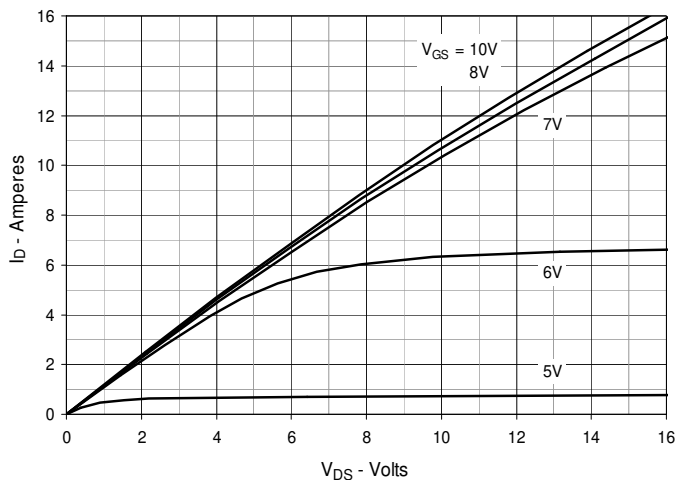
Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .



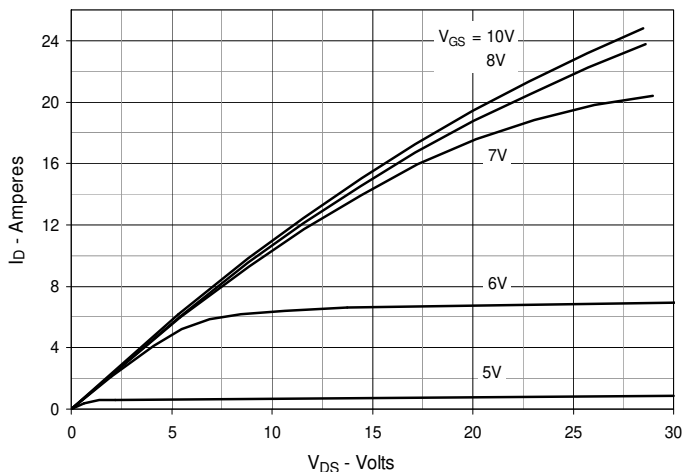
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

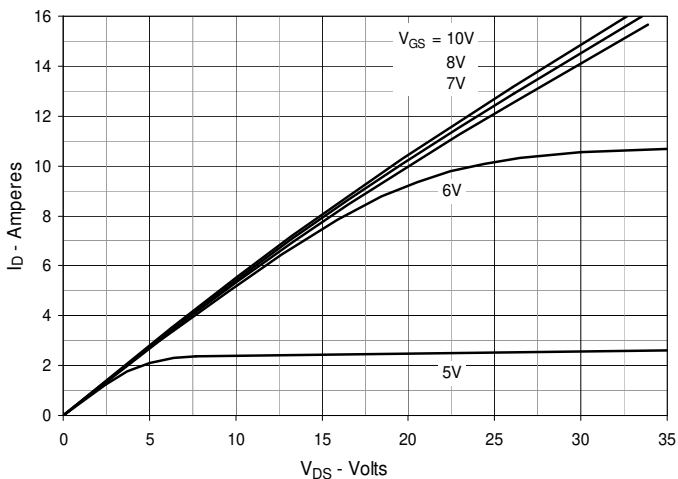
**Fig. 1. Output Characteristics  $T_J = @ 25^\circ\text{C}$**



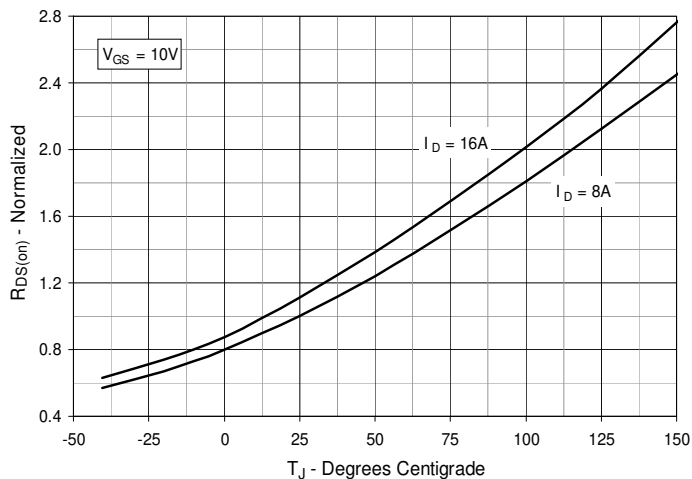
**Fig. 2. Extended Output Characteristics  $T_J = @ 25^\circ\text{C}$**



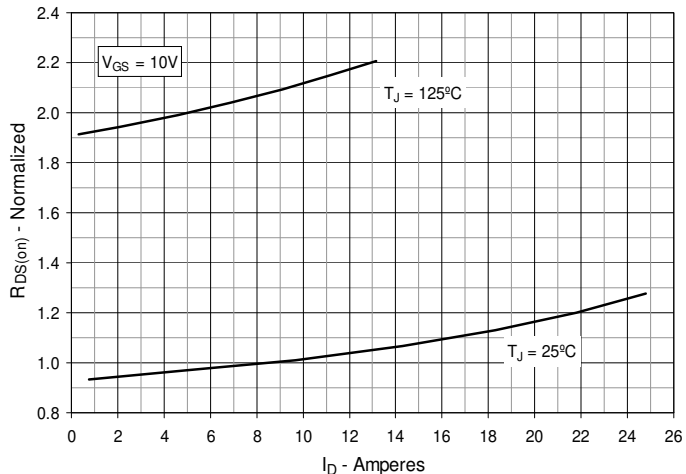
**Fig. 3. Output Characteristics  $T_J = @ 125^\circ\text{C}$**



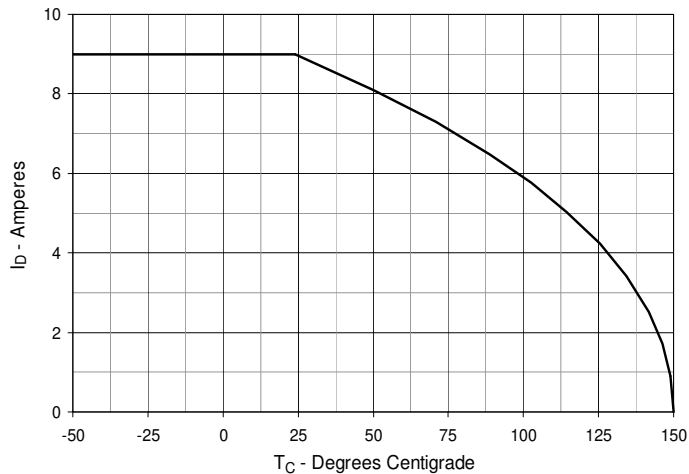
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 8\text{A}$  Value vs. Junction Temperature**



**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 8\text{A}$  Value vs. Drain Current**



**Fig. 6. Maximum Drain Current vs. Case Temperature**



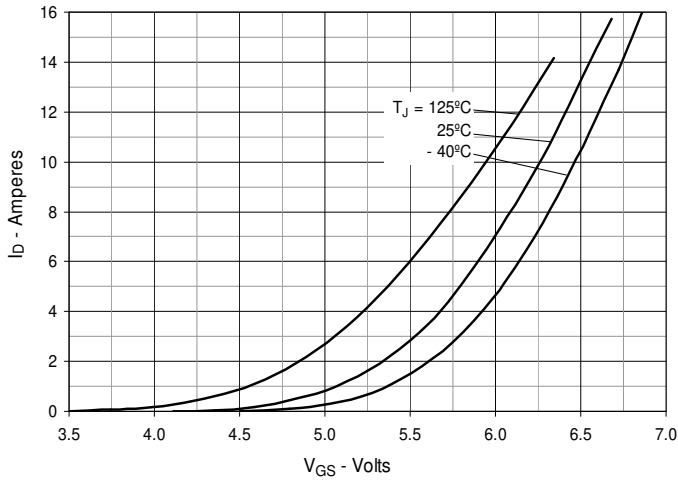
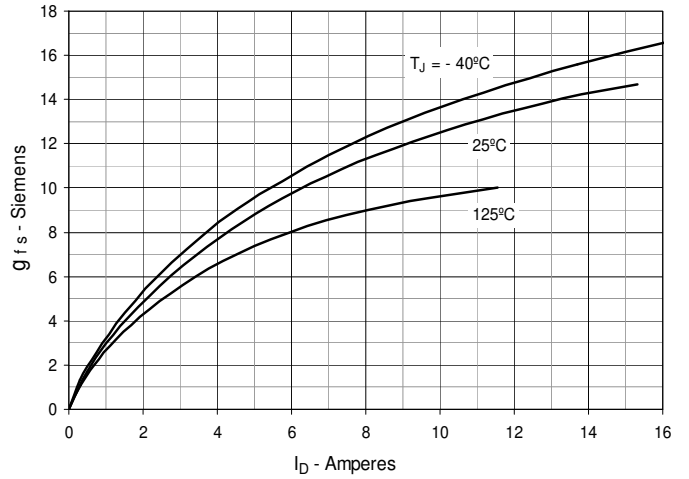
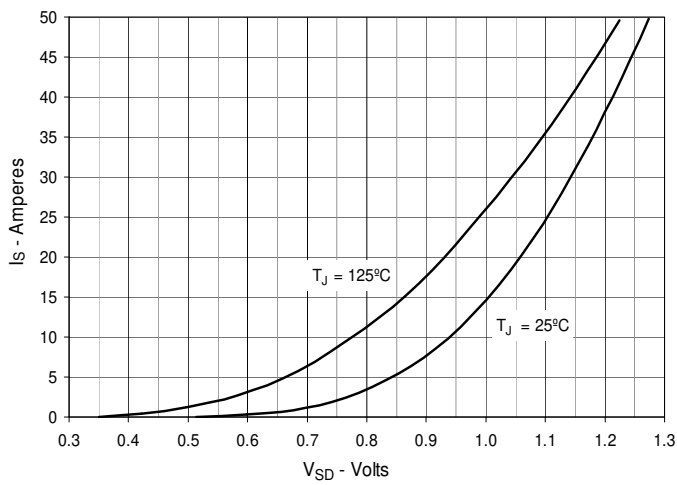
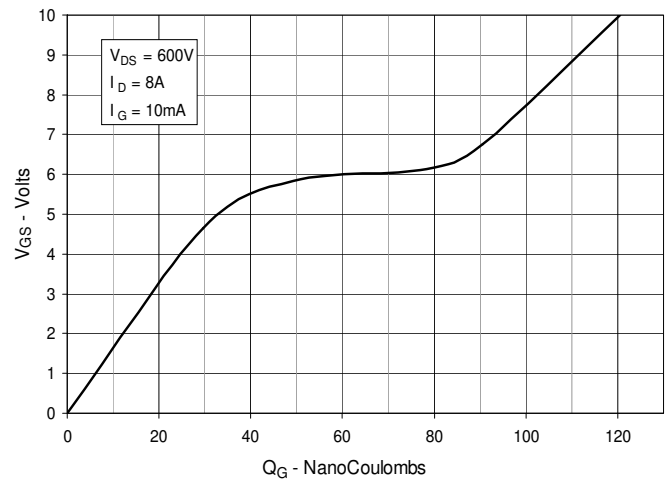
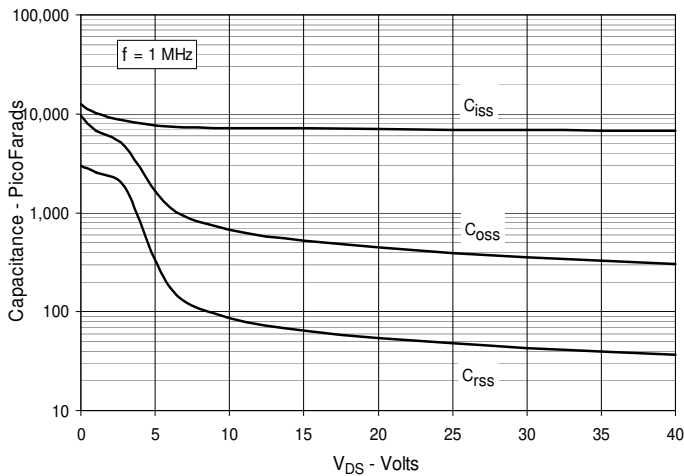
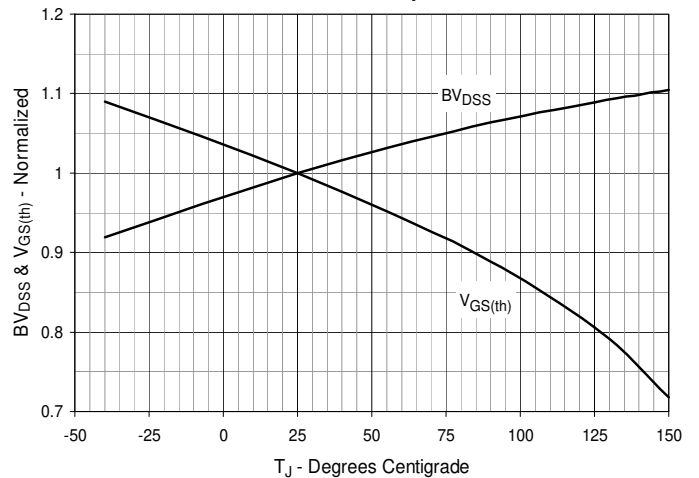
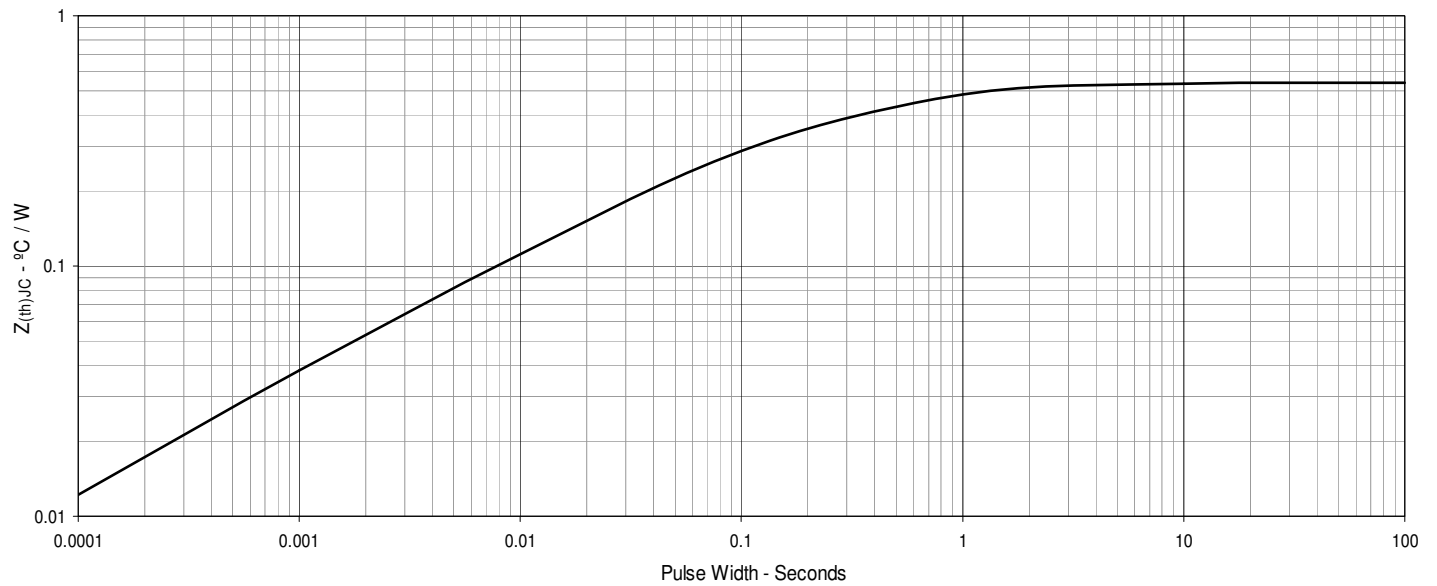
**Fig. 7. Input Admittance**

**Fig. 8. Transconductance**

**Fig. 9. Forward Voltage Drop of Intrinsic Diode**

**Fig. 10. Gate Charge**

**Fig. 11. Capacitance**

**Fig. 12. Breakdown and Threshold Voltages vs. Junction Temperature**


Fig. 13. Maximum Transient Thermal Impedance





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